NEC

MOS INTEGRATED CIRCUIT

μPD70F3003A, 70F3025A, 70F3003A(A)

V853™
32-BIT SINGLE-CHIP MICROCONTROLLERS

DESCRIPTION

The μPD70F3003A, μPD70F3025A, and μPD70F3003A(A) have a flash memory instead of the internal mask ROM of the μPD703003A/703004A, μPD703025A, and μPD703003A(A), respectively. This model is useful for small-scale production of a variety of application sets or early start of production since the program can be written and erased by the user even with the μPD70F3003 mounted on the board.

Detailed function descriptions are provided in the following user's manuals. Be sure to read them before designing.

V853 Hardware User's Manual: U10913E
V850 Series™ Architecture User's Manual: U10243E

FEATURES

- Compatible with μPD703003A, 703004A, 703025A, and 703003A(A)
  - Can be replaced with mask ROM model for mass production of application set
    μPD70F3003A → μPD703003A, 703004A
    μPD70F3025A → μPD703025A
    μPD70F3003A(A) → μPD703003A(A)
- Internal memory Flash memory: 128KB (μPD70F3003A, 70F3003A(A))
  256KB (μPD70F3025A)

Remark For differences among the products, refer to **1. DIFFERENCES BETWEEN PRODUCT**.

★ ORDERING INFORMATION

Part Number	Package	Quality Grade
μPD70F3003AGC-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3025AGC-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Standard
μPD70F3003AGC(A)-33-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Special

The μPD70F3003A and μPD70F3003A(A) differ in the quality grade only.

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

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Printed in Japan

The mark ★ shows major revised points.

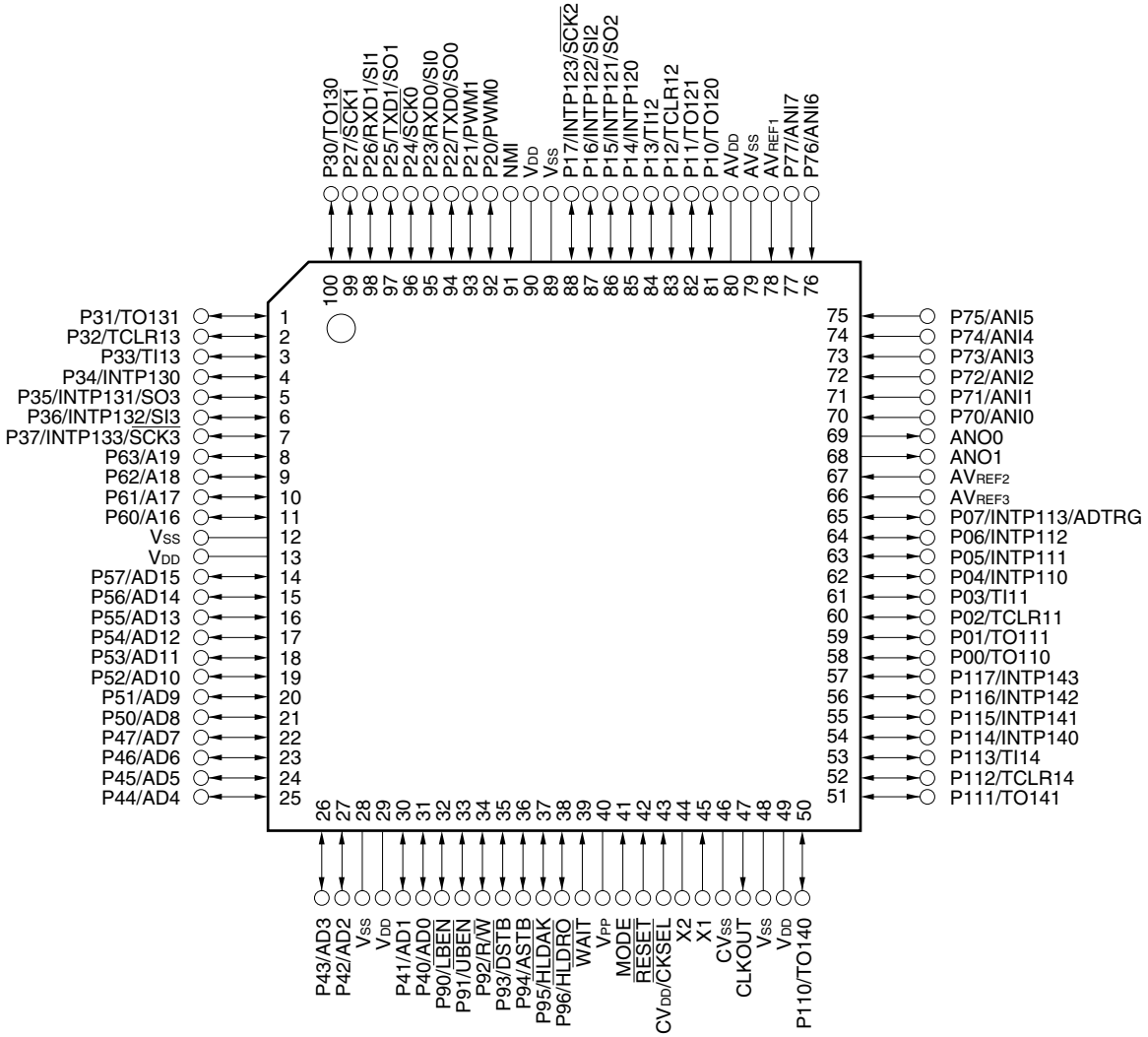
APPLICATIONS

μPD70F3003A, 70F3025A: Camcorders, VCRs, PPCs, LBPs, printers, motor controllers, NC machine tools, mobile telephones, etc.

μPD70F3003A(A): Medical equipment, automotive appliances, etc.

★ PIN CONFIGURATION (Top View)

- **100-Pin Plastic LQFP (fine pitch) (14 × 14)**
  μPD70F3003AGC-33-8EU μPD70F3025AGC-33-8EU
  μPD70F3003AGC(A)-33-8EU

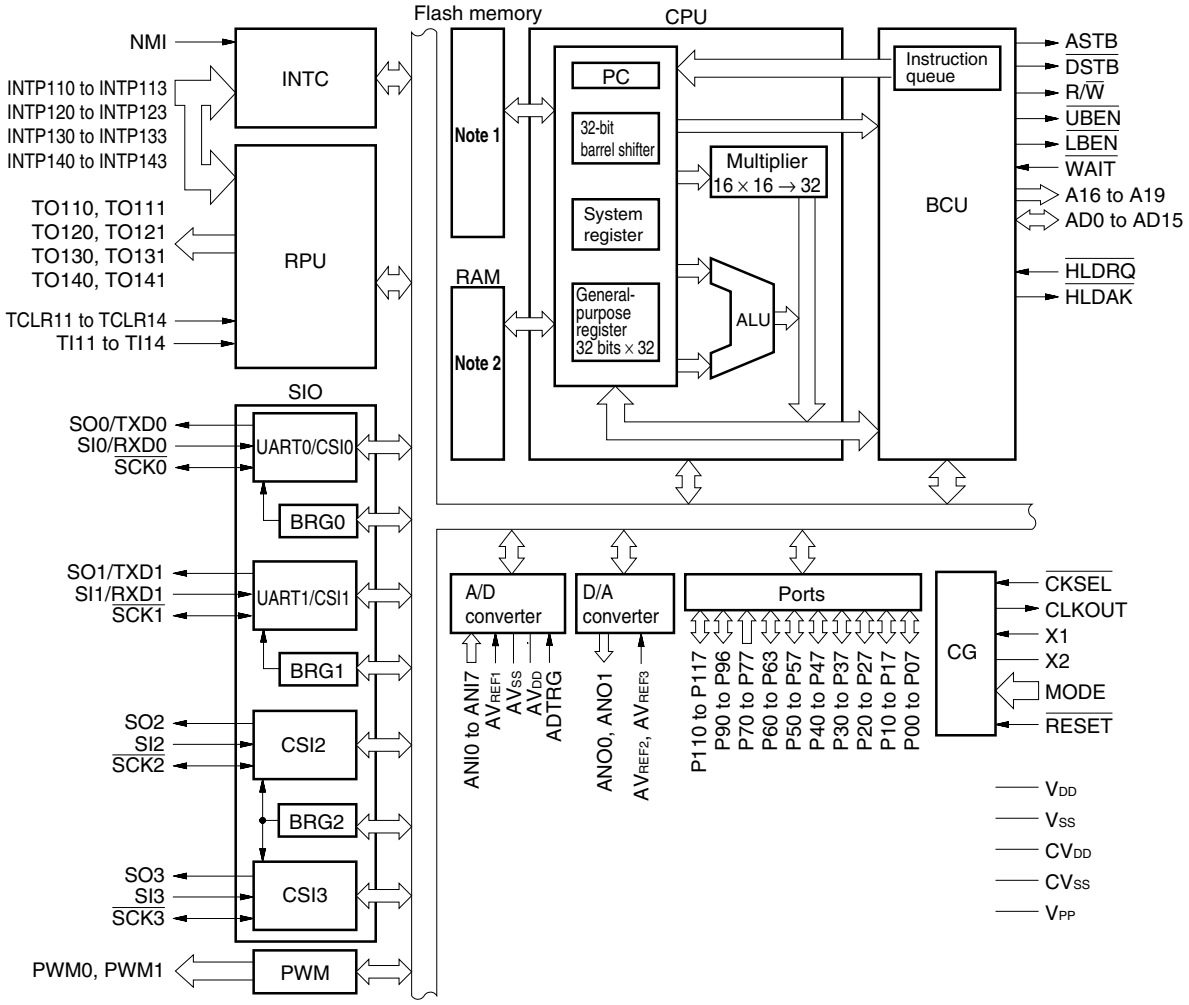


Caution Connect V_{PP} pin to V_{SS} pin except the case that μPD70F3003A, 70F3003A(A) or 70F3025A is used in flash memory programming mode.

PIN NAMES

A16 to A19:	Address bus
AD0 to AD15:	Address/data bus
ADTRG:	A/D Trigger input
ANI0 to ANI7:	Analog input
ANO0, ANO1:	Analog output
ASTB:	Address strobe
AV_{DD}:	Analog V_{DD}
AV_{REF1} to AV_{REF3}:	Analog reference voltage
AV_{SS}:	Analog V_{SS}
CV_{DD}:	Power supply for clock generator
CV_{SS}:	Ground for clock generator
$\overline{CKSEL}$:	Clock select
CLKOUT :	Clock output
$\overline{DSTB}$:	Data strobe
$\overline{HLDAK}$:	Hold acknowledge
$\overline{HLDRQ}$:	Hold request
INTP110 to INTP113, INTP120 to INTP123, INTP130 to INTP133, INTP140 to INTP143:	Interrupt request from peripherals
$\overline{LBEN}$:	Lower byte enable
MODE:	Mode
NMI:	Non-maskable interrupt request
P00 to P07:	Port 0
P10 to P17:	Port 1
P20 to P27:	Port 2
P30 to P37:	Port 3
P40 to P47:	Port 4
P50 to P57:	Port 5
P60 to P63:	Port 6
P70 to P77:	Port 7
P90 to P96:	Port 9
P110 to P117:	Port 11
PWM0, PWM1:	Pulse width modulation
$\overline{RESET}$:	Reset
R/$\overline{W}$:	Read/write status
RXD0, PXD1:	Receive data
$\overline{SCK0}$ to $\overline{SCK3}$:	Serial clock
SI0 to SI3:	Serial input
SO0 to SO3:	Serial output
TO110, TO111, TO120, TO121, TO130, TO131, TO140, TO141:	Timer output
TCLR11 to TCLR14:	Timer clear
TI11 to TI14:	Timer input
TXD0, TXD1:	Transmit data
$\overline{UBEN}$:	Upper byte enable
$\overline{WAIT}$:	Wait
X1, X2:	Crystal
V_{DD}:	Power supply
V_{PP}:	Programming power supply
V_{SS}:	Ground

INTERNAL BLOCK DIAGRAM



Notes 1. μPD70F3003A, 70F3003A(A): 128 KB
μPD70F3025A: 256 KB

2. μPD70F3003A, 70F3003A(A): 4 KB
μPD70F3025A: 8 KB

CONTENTS

1. DIFFERENCES BETWEEN PRODUCTS

Item	μPD703003A	μPD703004A	μPD703025A	μPD703003A(A)	μPD703025A(A)	μPD70F3003A	μPD70F3025A	μPD70F3003A(A)
Internal ROM	Mask ROM					Flash memory		
	128 KB	96 KB	256 KB	128 KB	256 KB	128 KB	256 KB	128 KB
Internal RAM	4 KB		8 KB	4 KB	8 KB	4 KB	8 KB	4 KB
Flash memory programming mode	None					Provided		
V_{PP} pin	None					Provided		
Quality grade	Standard			Special		Standard		Special
Electrical specifications	Current consumption, etc. differs. (Refer to each product data sheets).							
Others	Noise immunity and noise radiation differ because circuit scale and mask layout differ.							

Caution There are differences in noise immunity and noise radiation between the flash memory version and mask ROM version. When pre-producing an application set with the flash memory version and then mass-producing it with the mask ROM version, be sure to conduct sufficient evaluation for commercial samples (not engineering samples) of the mask ROM version.

2. PIN FUNCTIONS

2.1 Port Pins

(1/2)

Pin Name	I/O	Function	Alternate Function
P00	I/O	Port 0	TO110
P01		8-bit I/O port.	TO111
P02		Input/output can be specified in 1-bit units.	TCLR11
P03			TI11
P04			INTP110
P05			INTP111
P06			INTP112
P07			INTP113/ADTRG
P10	I/O	Port 1	TO120
P11		8-bit I/O port.	TO121
P12		Input/output can be specified in 1-bit units.	TCLR12
P13			TI12
P14			INTP120
P15			INTP121/SO2
P16			INTP122/SI2
P17			INTP123/$\overline{\text{SCK2}}$
P20	I/O	Port 2	PWM0
P21		8-bit I/O port.	PWM1
P22		Input/output can be specified in 1-bit units.	TXD0/SO0
P23			RXD0/SI0
P24			$\overline{\text{SCK0}}$
P25			TXD1/SO1
P26			RXD1/SI1
P27			$\overline{\text{SCK1}}$
P30	I/O	Port 3	TO130
P31		8-bit I/O port.	TO131
P32		Input/output can be specified in 1-bit units.	TCLR13
P33			TI13
P34			INTP130
P35			INTP131/SO3
P36			INTP132/SI3
P37			INTP133/$\overline{\text{SCK3}}$
P40 to P47	I/O	Port 4 8-bit I/O port. Input/output can be specified in 1-bit units.	AD0 to AD7
P50 to P57	I/O	Port 5 8-bit I/O port. Input/output can be specified in 1-bit units.	AD8 to AD15

(2/2)

Pin Name	I/O	Function	Alternate Function
P60 to P63	I/O	Port 6 4-bit I/O port. Input/output can be specified in 1-bit units.	A16 to A19
P70 to P77	Input	Port 7 8-bit input port.	ANI0 to ANI7
P90	I/O	Port 9 7-bit I/O port. Input/output can be specified in 1-bit units.	$\overline{\text{LBEN}}$
P91			$\overline{\text{UBEN}}$
P92			R/$\overline{\text{W}}$
P93			$\overline{\text{DSTB}}$
P94			ASTB
P95			$\overline{\text{HLDAK}}$
P96			$\overline{\text{HLDRQ}}$
P110	I/O	Port 11 8-bit I/O port. Input/output can be specified in 1-bit units.	TO140
P111			TO141
P112			TCLR14
P113			TI14
P114			INTP140
P115			INTP141
P116			INTP142
P117			INTP143

2.2 Non-Port Pins

(1/2)

Pin Name	I/O	Function	Alternate Function
TO110	Output	Pulse signal output from timers 11 to 14	P00
TO111			P01
TO120			P10
TO121			P11
TO130			P30
TO131			P31
TO140			P110
TO141			P111
TCLR11	Input	External clear signal input for timers 11 to 14	P02
TCLR12			P12
TCLR13			P32
TCLR14			P112
TI11	Input	External count clock input for timers 11 to 14	P03
TI12			P13
TI13			P33
TI14			P113
INTP110	Input	External maskable interrupt request input and external capture trigger input for timer 11	P04
INTP111			P05
INTP112			P06
INTP113			P07/ADTRG
INTP120	Input	External maskable interrupt request input and external capture trigger input for timer 12	P14
INTP121			P15/SO2
INTP122			P16/S12
INTP123			P17/$\overline{\text{SCK2}}$
INTP130	Input	External maskable interrupt request input and external capture trigger input for timer 13	P34
INTP131			P35/SO3
INTP132			P36/SI3
INTP133			P37/$\overline{\text{SCK3}}$
INTP140	Input	External maskable interrupt request input and external capture trigger input for timer 14	P114
INTP141			P115
INTP142			P116
INTP143			P117
SO0	Output	Serial transmit data output for CSI0 to CSI3 (3-wire)	P22/TXD0
SO1			P25/TXD1
SO2			P15/INTP121
SO3			P35/INTP131
SI0	Input	Serial receive data output for CSI0 to CSI3 (3-wire)	P23/RXD0
SI1			P26/RXD1
SI2			P16/INTP122
SI3			P36/INTP132

(2/2)

Pin Name	I/O	Function	Alternate Function
$\overline{SCK0}$	I/O	Serial clock I/O for CSI0 to CSI3 (3-wire)	P24
$\overline{SCK1}$			P27
$\overline{SCK2}$			P17/INTP123
$\overline{SCK3}$			P37/INTP133
TXD0	Output	Serial transmit data output of UART0 to UART1	P22/SO0
TXD1			P25/SO1
RXD0	Input	Serial receive data input of UART0 to UART1	P23/SI0
RXD1			P26/SI1
PWM0	Output	Pulse signal output of PWM	P20
PWM1			P21
AD0 to AD7	I/O	16-bit multiplexed address/data bus when external memory is connected	P40 to P47
AD8 to AD15			P50 to P57
A16 to A19	Output	Higher address bus when external memory is connected	P60 to P63
$\overline{LBEN}$	Output	Lower byte enable signal output of external data bus	P90
$\overline{UBEN}$		Higher byte enable signal output of external data bus	P91
R/$\overline{W}$	Output	External read/write status output	P92
$\overline{DSTB}$		External data strobe signal output	P93
ASTB		External address strobe signal output	P94
$\overline{HLDAK}$	Output	Bus hold acknowledge output	P95
$\overline{HLDRQ}$	Input	Bus hold request input	P96
ANI0 to ANI7	Input	Analog input to A/D converter	P70 to P77
ANO0, ANO1	Output	Analog output of D/A converter	—
NMI	Input	Non-maskable interrupt request input	—
CLKOUT	Output	System clock output	—
$\overline{CKSEL}$	Input	Input specifying operation mode of clock generator	CV_{DD}
$\overline{WAIT}$	Input	Control signal input inserting wait state in bus cycle	—
MODE	Input	Operation mode specification	—
$\overline{RESET}$	Input	System reset input	—
X1	Input	System clock resonator connection. Input external clock to X1 to	—
X2	—	supply external clock.	—
ADTRG	Input	A/D converter external trigger input	P07/INTP113
AV_{REF1}	Input	Reference voltage input for A/D converter	—
AV_{REF2}	Input	Reference voltage input for D/A converter	—
AV_{REF3}			—
AV_{DD}	—	Positive power supply for A/D converter	—
AV_{SS}	—	Ground potential for A/D converter	—
CV_{DD}	—	Positive power supply for internal clock generator	$\overline{CKSEL}$
CV_{SS}	—	Ground potential for internal clock generator	—
V_{DD}	—	Positive power supply	—
V_{SS}	—	Ground potential	—
V_{PP}	—	High voltage application pin when program is written/verified	—

2.3 Pin I/O Circuits and Recommended Connection of Unused Pins

Table 2-1 shows the I/O circuit type of each pin, and the recommended connections of the unused pins. Figure 2-1 shows a partially simplified diagram of each circuit.

It is recommended that 1 to 10 kΩ resistors be used when connecting to V_{DD} or V_{SS} via a resistor.

Table 2-1. Types of Pin I/O Circuits and Recommended Connections of Unused Pins (1/2)

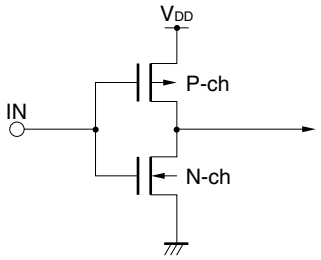
Pin Name	I/O Circuit Type	Recommended Connection of Unused Pins
P00/TO110, P01/TO111	5	Input: Independently connect to V_{DD} or V_{SS} via a resistor. Output: Leave open.
P02/TCLR11, P03/TI11, P04/INTP110 to P07/INTP113/ADTRG	8	
P10 to TO120, P11/TO121	5	
P12/TCLR12, P13/TI12 P14/INTP120 P15/INTP121/SO2 P16/INTP122/SI2 P17/INTP123/$\overline{SCK2}$	8	
P20/PWM0, P21/PWM1 P22/TXD0/SO0	5	
P23/RXD0/SI0, P24/$\overline{SCK0}$	8	
P25/TXD1/SO1	5	
P26/RXD1/SI1, P27/$\overline{SCK1}$	8	
P30/TO130, P31/TO131	5	
P32/TCLR13, P33/TI13 P34/INTP130	8	
P35/INTP131/SO3 P36/INTP132/SI3 P37/INTP133/$\overline{SCK3}$	10-A	
P40/AD0 to P47/AD7	5	
P50/AD8 to P57/AD15		
P60/A16 to P63/A19		
P70/ANI0 to P77/ANI7	9	Directly connect to V_{SS}.
P90/$\overline{LBEN}$	5	Input: Independently connect to V_{DD} or V_{SS} via a resistor. Output: Leave open.
P91/$\overline{UBEN}$		
P92/R/$\overline{W}$		
P93/$\overline{DSTB}$		
P94/ASTB		
P95/$\overline{HLDAK}$		
P96/$\overline{HLDRQ}$		
P110/TO140, P111/TO141		
P112/TCLR14, P113/TI14 P114/INTP140 to P117/INTP143	8	

Table 2-1. Types of Pin I/O Circuits and Recommended Connection of Unused Pins (2/2)

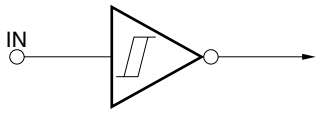
Pin Name	I/O Circuit Type	Recommended Connection of Unused Pins
ANO0, ANO1	12	Leave open.
NMI	2	Directly connect to V_{SS}.
CLKOUT	3	Leave open.
$\overline{WAIT}$	1	Directly connect to V_{DD}.
MODE	2	—
$\overline{RESET}$		
$CV_{DD}/\overline{CKSEL}$		—
AV_{REF1} to AV_{REF3}, AV_{SS}	—	Directly connect to V_{SS}.
AV_{DD}	—	Directly connect to V_{DD}.
V_{PP}	—	Connect to V_{SS}.

Figure 2-1. Pins I/O Circuits

Type 1

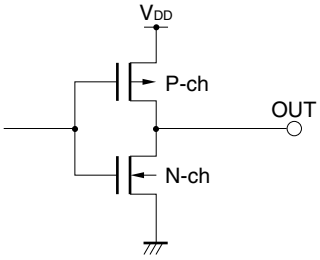


Type 2

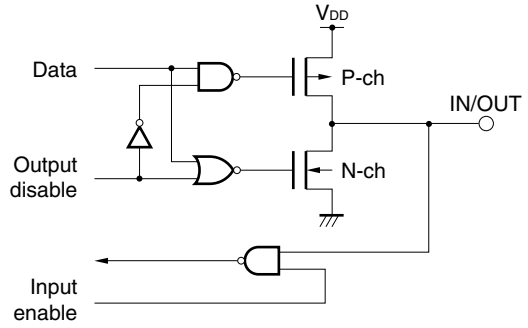


Schmitt trigger input with hysteresis characteristics

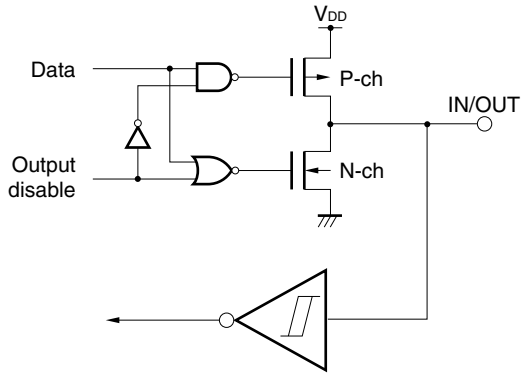
Type 3



Type 5



Type 8



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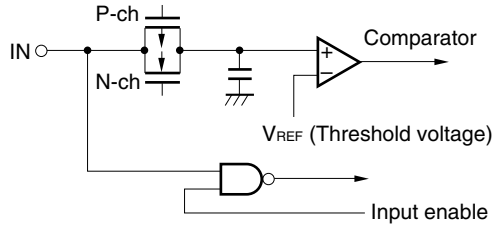
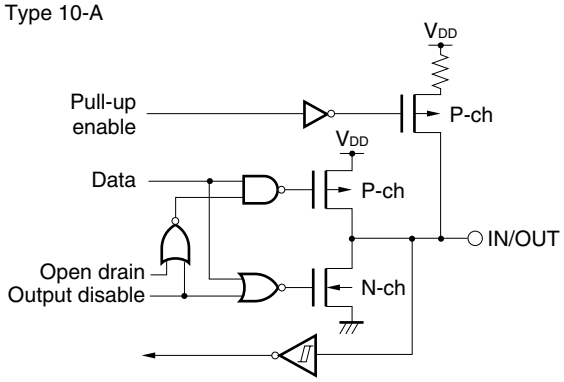
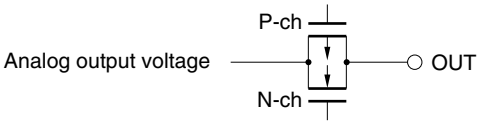


Type 10-A



Type 12



3. ELECTRICAL SPECIFICATIONS

3.1 Normal Operation Mode

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbol	Conditions		Ratings	Unit
Supply voltage	V_{DD}	V_{DD} pin		–0.5 to +7.0	V
	CV_{DD}	CV_{DD} pin		–0.5 to V_{DD} + 0.3[Note 1]	V
	CV_{SS}	CV_{SS} pin		–0.5 to +0.5	V
	AV_{DD}	AV_{DD} pin		–0.5 to V_{DD} + 0.3[Note 1]	V
	AV_{SS}	AV_{SS} pin		–0.5 to +0.5	V
Input voltage	V_{I1}	**Note 2**, V_{DD} = 5.0 V ±10%		–0.5 to V_{DD} + 0.3[Note 1]	V
	V_{I2}	V_{PP} pin in flash memory programming mode, V_{DD} = 5.0 V ±10%		–0.5 to +11.0	V
Clock input voltage	V_K	X1 pin, V_{DD} = 5.0 V ±10%		–0.5 to V_{DD} + 1.0[Note 1]	V
Output current, low	I_{CL}	1 pin		4.0	mA
		Total of all pins		100	mA
Output current, high	I_{CH}	1 pin		–4.0	mA
		Total of all pins		–100	mA
Output voltage	V_O	V_{DD} = 5.0 V ±10%		–0.5 to V_{DD} + 0.3[Note 1]	V
Analog input voltage	V_{IAN}	P70/ANI0 to P77/ANI7	$AV_{DD} > V_{DD}$	–0.5 to V_{DD} + 0.3[Note 1]	V
			$V_{DD} \geq AV_{DD}$	–0.5 to AV_{DD} + 0.3[Note 1]	V
Analog reference input voltage	AV_{REF}	AV_{REF1} to AV_{REF3}	$AV_{DD} > V_{DD}$	–0.5 to V_{DD} + 0.3[Note 1]	V
			$V_{DD} \geq AV_{DD}$	–0.5 to AV_{DD} + 0.3[Note 1]	V
Operating ambient temperature	T_A			–40 to +85	°C
Storage temperature	T_{stg}			–65 to +125	°C

Notes 1. Be sure not to exceed the absolute maximum ratings (MAX. value) of each supply voltage.

2. X1, P70 to P77, AV_{REF1} to AV_{REF3}, and their alternate-function pins are excluded.

Cautions 1. Avoid direct connections among the IC device output (or I/O) pins and between V_{DD} or V_{CC} and GND. However, direct connections among open-drain and open-collector pins are possible, as are direct connections to external circuits that have timing designed to prevent output conflict with pins that become high-impedance.

2. Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

The normal operating ranges of ratings and conditions in which the quality of the product is guaranteed are specified in the following DC Characteristics and AC Characteristics.

Capacitance (T_A = 25°C, V_{DD} = V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C_I	fc = 1 MHz			15	pF
I/O capacitance	C_{IO}	Pins other than tested pin: 0 V			15	pF
Output capacitance	C_O				15	pF

Operating Conditions

Operation Mode	Internal System Clock Frequency (ϕ)	Operating Temperature (T_A)	Supply Voltage (V_{DD})
Direct mode, PLL mode	2 to 33 MHz[Note 1]	–40 to +85°C	5.0 V ±10%
	5 to 33 MHz[Note 2]	–40 to +85°C	5.0 V ±10%

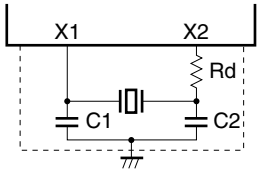
Notes 1. When A/D converter not used.
2. When A/D converter used.

Recommended Oscillator

Caution For the resonator selection and oscillator constant of the μPD70F3003A(A), customers are requested to apply to the resonator manufacturer for evaluation.

(1) Ceramic resonator connection (T_A = –40 to +85°C)

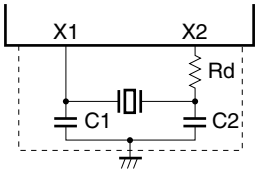
(a) μPD70F3003A



Manufacturer	Part Number	Oscillation Frequency f_{XX} (MHz)	Recommended Circuit Constant			Oscillation Voltage Range		Oscillation Stabilization Time (MAX.) T_{OST} (ms)
			C1 (pF)	C2 (pF)	R_d (W)	MIN. (V)	MAX. (V)	
Kyocera Corporation	PBRC4.00HR	4.0	On-chip	On-chip	—	4.5	5.5	0.10
	PBRC5.00HR	5.0	On-chip	On-chip	—	4.5	5.5	0.08
	PBRC6.00HR	6.0	On-chip	On-chip	—	4.5	5.5	0.08
	PBRC6.60HR	6.6	On-chip	On-chip	—	4.5	5.5	0.08
TDK	FCR4.0MC5	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR5.0MC5	5.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR6.0MC5	6.0	On-chip	On-chip	—	4.5	5.5	0.11
Murata Mfg. Co., Ltd	CSTS0400MG06	4.0	On-chip	On-chip	—	4.5	5.5	0.12
	CSTCR4M00G05	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTS0600MG06	6.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTCR6M00G55-R0	6.0	On-chip	On-chip	—	4.5	5.5	0.18

Cautions 1. Connect the oscillator as closely to the X1 and X2 pins as possible.
2. Do not wire any other signal lines in the area indicated by the broken lines.
3. Thoroughly evaluate the matching between the μPD70F3003A and the resonator.

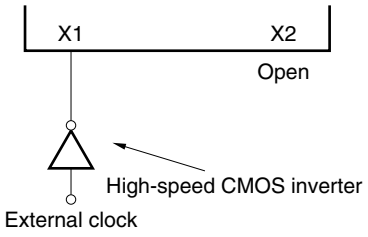
(b) μPD70F3025A



Manufacturer	Part Number	Oscillation Frequency f_{XX} (MHz)	Recommended Circuit Constant			Oscillation Voltage Range		Oscillation Stabilization Time (MAX.) T_{OST} (ms)
			C1 (pF)	C2 (pF)	R_d (W)	MIN. (V)	MAX. (V)	
Kyocera Corporation	PBRC4.00HR	4.0	On-chip	On-chip	—	4.5	5.5	0.12
	PBRC5.00HR	5.0	On-chip	On-chip	—	4.5	5.5	0.04
	PBRC6.00HR	6.0	On-chip	On-chip	—	4.5	5.5	0.04
	PBRC6.60HR	6.6	On-chip	On-chip	—	4.5	5.5	0.04
TDK	FCR4.0MC5	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	FCR5.0MC5	5.0	On-chip	On-chip	—	4.5	5.5	0.13
	FCR6.0MC5	6.0	On-chip	On-chip	—	4.5	5.5	0.13
Murata Mfg. Co., Ltd	CSTS0400MG06	4.0	On-chip	On-chip	—	4.5	5.5	0.12
	CSTCR4M00G55-R0	4.0	On-chip	On-chip	—	4.5	5.5	0.14
	CSTS0600MG06	6.0	On-chip	On-chip	—	4.5	5.5	0.16
	CSTCR6M00G55-R0	6.0	On-chip	On-chip	—	4.5	5.5	0.19

Cautions 1. Connect the oscillator as closely to the X1 and X2 pins as possible.
2. Do not wire any other signal lines in the area indicated by the broken lines.
3. Thoroughly evaluate the matching between the μPD70F3025A and the resonator.

(2) External clock input



Cautions 1. Put the high-speed CMOS inverter as close to the X1 pins as possible.
2. Sufficiently evaluate the matching between the μPD70F3003A, 70F3025A, or 70F3003A(A), and the high-speed CMOS inverter.

DC Characteristics (T_A = –40 to +85°C, V_{DD} = 5.0 V ±10%, V_{SS} = 0 V)

(1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH}	Except X1 and **Note**	2.2		V_{DD} + 0.3	V
		Note	0.8V_{DD}		V_{DD} + 0.3	V
Input voltage, low	V_{IL}	Except X1 and **Note**	–0.5		+0.8	V
		Note	–0.5		0.2V_{DD}	V
Clock input voltage, high	V_{XH}	X1	0.8V_{DD}		V_{DD} + 0.5	V
Clock input voltage, low	V_{XL}	X1	–0.5		0.6	V
Schmitt trigger input threshold voltage	V_T^+	**Note**, rising		3.0		V
	V_T^-	**Note**, falling		2.0		V
Schmitt trigger input hysteresis width	$V_T^+ - V_T^-$	**Note**	0.5			V
Output voltage, high	V_{OH}	I_{OH} = –2.5 mA	0.7V_{DD}			V
		I_{OH} = –100 μA	V_{DD} – 0.4			V
Output voltage, low	V_{OL}	I_{OC} = 2.5 mA			0.45	V
Input leakage current, high	I_{LIH}	V_I = V_{DD}			10	μA
Input leakage current, low	I_{LIL}	V_I = 0 V			–10	μA
Output leakage current, high	I_{LOH}	V_O = V_{DD}			10	μA
Output leakage current, low	I_{LOL}	V_O = 0 V			–10	μA
Software pull-up resistor	R	P35/INTP131/SO3, P36/INTP132/SI3, P37/INTP133/$\overline{SCK3}$	15	40	90	kΩ

Note P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{RESET}$, NMI, MODE, and their alternate-function pins.

Remark TYP. values are reference values for when T_A = 25°C and V_{DD} = 5.0 V.

(2/2)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply current	μPD70F3003A, 70F3003A(A)	Operating	I_{DD1}	Direct mode		2.2 × ϕ + 7.5	2.5 × ϕ + 22	mA
				PLL mode		2.3 × ϕ + 9.5	2.6 × ϕ + 25	mA
		In HALT mode	I_{DD2}	Direct mode		1.2 × ϕ + 7.5	1.3 × ϕ + 15	mA
				PLL mode		1.3 × ϕ + 9.5	1.4 × ϕ + 17	mA
		In IDLE mode	I_{DD3}	Direct mode		8 × ϕ + 300	10 × ϕ + 500	μA
				PLL mode		0.1 × ϕ + 2	0.2 × ϕ + 3	mA
		In STOP mode	I_{DD4}	CESEL = 0, **Note 1**		2	50	μA
				CESEL = 0, **Note 2**		2	200	μA
				CESEL = 1, **Note 1**		30	200	μA
				CESEL = 1, **Note 2**		30	500	μA
	μPD70F3025A	Operating	I_{DD1}	Direct mode		2.5 × ϕ + 8	2.8 × ϕ + 22.5	mA
				PLL mode		2.6 × ϕ + 10	2.9 × ϕ + 25.5	mA
		In HALT mode	I_{DD2}	Direct mode		1.3 × ϕ + 7.5	1.4 × ϕ + 15	mA
				PLL mode		1.3 × ϕ + 12.5	1.4 × ϕ + 20	mA
		In IDLE mode	I_{DD3}	Direct mode		8 × ϕ + 300	10 × ϕ + 500	μA
				PLL mode		0.1 × ϕ + 2	0.2 × ϕ + 3	mA
		In STOP mode	I_{DD4}	CESEL = 0, **Note 1**		2	50	μA
				CESEL = 0, **Note 2**		2	200	μA
				CESEL = 1, **Note 1**		60	300	μA
				CESEL = 1, **Note 2**		60	500	μA

Notes 1. $-40°C \le T_A \le +50°C$

2. $50°C < T_A \le 85°C$

Remarks 1. TYP. values are reference values for when $T_A = 25°C$ (except for the conditions in **Note 2**) and $V_{DD} = 5.0$ V. The power supply current does not include AV_{REF1} to AV_{REF3} or the current that flows through software pull-up resistors.

2. ϕ: Internal system clock frequency

Data Retention Characteristics (T_A = –40 to +85°C, V_{DD} = V_{DDDR})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Data hold voltage	V_{DDDR}	STOP mode		1.5		5.5	V
Data hold current	I_{DDDR}	μPD70F3003A, 70F3003A(A)	CESEL = 0, **Note 1**		0.4V_{DDDR}	50	μA
			CESEL = 0, **Note 2**		0.4V_{DDDR}	200	μA
			CESEL = 1, **Note 1**		6V_{DDDR}	200	μA
			CESEL = 1, **Note 2**		6V_{DDDR}	500	μA
		μPD70F3025A	CESEL = 0, **Note 1**		0.4V_{DDDR}	50	μA
			CESEL = 0, **Note 2**		0.4V_{DDDR}	200	μA
			CESEL = 1, **Note 1**		12V_{DDDR}	300	μA
			CESEL = 1, **Note 2**		12V_{DDDR}	500	μA
Supply voltage rise time	t_{RVD}			200			μs
Supply voltage fall time	t_{FVD}			200			μs
Supply voltage hold time (vs. STOP mode setting)	t_{HVD}			0			ms
STOP mode release signal input time	t_{DREL}			0			ns
Data hold input voltage, high	V_{IHDR}	**Note 3**		0.9V_{DDDR}		V_{DDDR}	V
Data hold input voltage, low	V_{ILDR}	**Note 3**		0		0.1V_{DDDR}	V

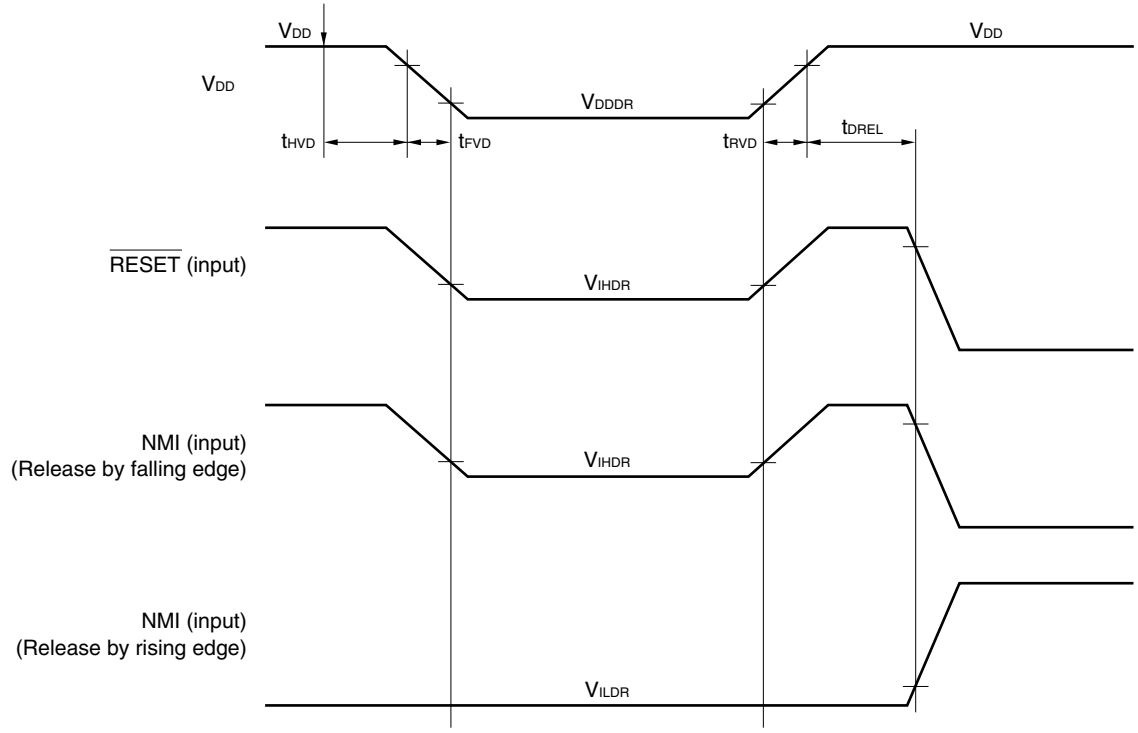
Notes 1. –40°C ≤ T_A ≤ +50°C

2. 50°C < T_A ≤ 85°C

3. P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{\text{RESET}}$, NMI, MODE, X1, and their alternate-function pins.

Remark TYP. values are reference values for when T_A = 25°C (except for the conditions in **Note 2**) and V_{DD} = 5.0 V.

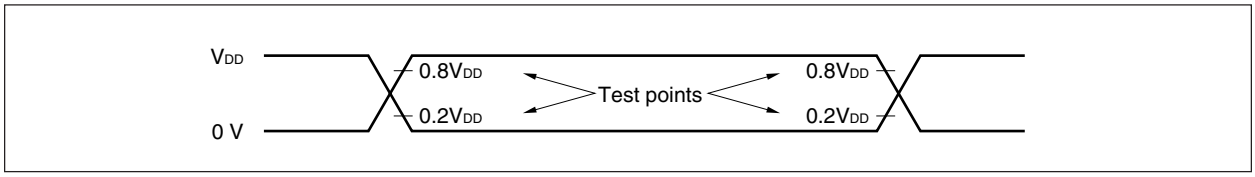
STOP mode is set (at fifth clock after PSC register has been set).



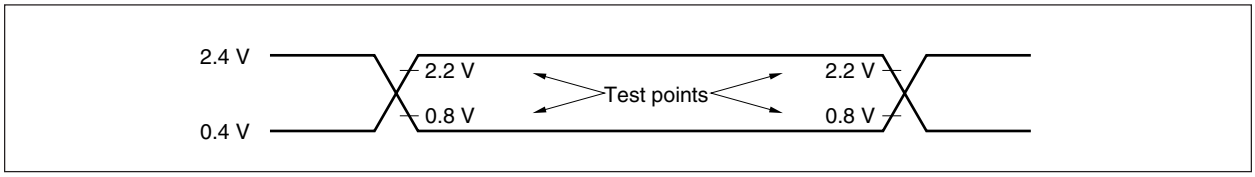
AC Characteristics (T_A = –40 to +85°C, V_{DD} = 5.0 V ±10%, V_{SS} = 0 V)

AC test input test points

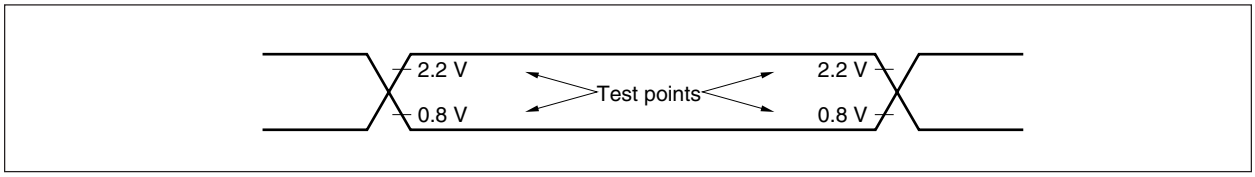
(a) P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{\text{RESET}}$, NMI, MODE, X1, and their alternate-function pins



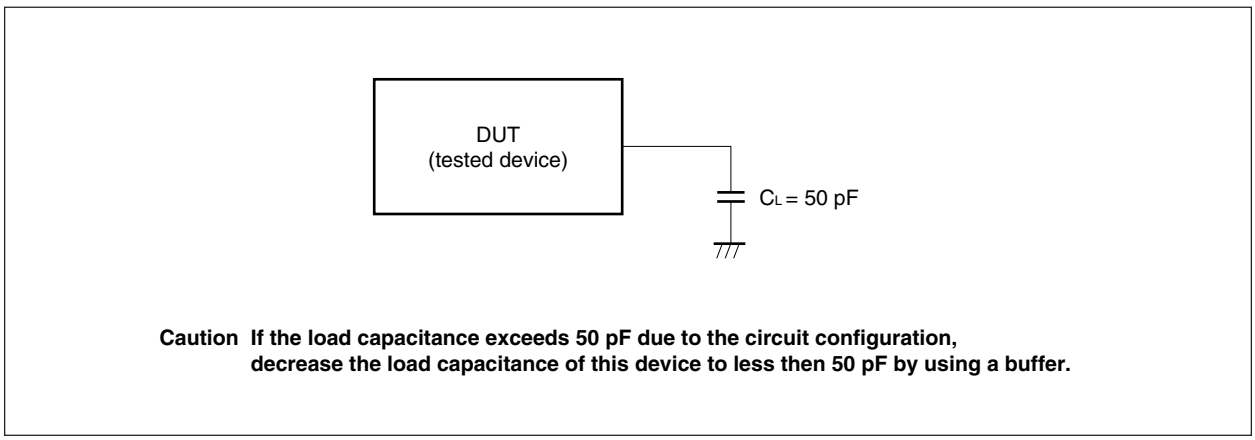
(b) Other than (a)



AC test output test points



Load condition



Caution If the load capacitance exceeds 50 pF due to the circuit configuration, decrease the load capacitance of this device to less then 50 pF by using a buffer.

(1) Clock timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
X1 input cycle	<1>	t_{CYX}	Direct mode	15	**Note 1**	ns
			PLL mode (PLL lock status)	151 Note 2	**Note 3**	ns
X1 input width, high	<2>	t_{WXH}	Direct mode	6		ns
			PLL mode	60		ns
X1 input width, low	<3>	t_{WXL}	Direct mode	6		ns
			PLL mode	60		ns
X1 input rise time	<4>	t_{XR}	Direct mode		7	ns
			PLL mode		10	ns
X1 input fall time	<5>	t_{XF}	Direct mode		7	ns
			PLL mode		10	ns
CPU operating frequency	—	ϕ		**Note 4**	33	MHz
CLKOUT output cycle	<6>	t_{CYK}		30	**Note 5**	ns
CLKOUT width, high	<7>	t_{WKH}		0.5 T – 5		ns
CLKOUT width, low	<8>	t_{WKL}		0.5 T – 5		ns
CLKOUT rise time	<9>	t_{XR}			5	ns
CLKOUT fall time	<10>	t_{XF}			5	ns
X1 ↓→ CLKOUT delay time	<11>	t_{DXK}	Direct mode	3	17	ns

Notes 1. When A/D converter used: 100 ns
When A/D converter not used: 250 ns

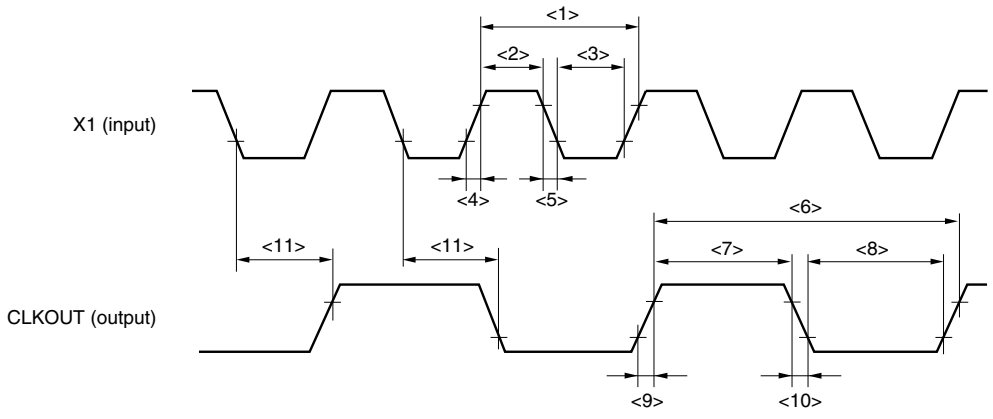
2. When using A/D converter: The value when $\phi = 5 \times f_{XX}$ and $\phi = f_{XX}$ are set. Setting $\phi = 1/2 \times f_{XX}$ is prohibited.
When not using A/D converter: The value when $\phi = 5 \times f_{XX}$, $\phi = f_{XX}$, and $\phi = 1/2 \times f_{XX}$ are set.

3. When using A/D converter: 250 ns (when $\phi = 5 \times f_{XX}$ is set) and 200 ns (when $\phi = f_{XX}$ is set). Setting $\phi = 1/2 \times f_{XX}$ is prohibited.
When not using A/D converter: 250 ns (when $\phi = 5 \times f_{XX}$, $\phi = f_{XX}$, and $\phi = 1/2 \times f_{XX}$ are set).

4. When A/D converter used: 5 MHz
When A/D converter not used: 2 MHz

5. When A/D converter used: 200 ns
When A/D converter not used: 500 ns

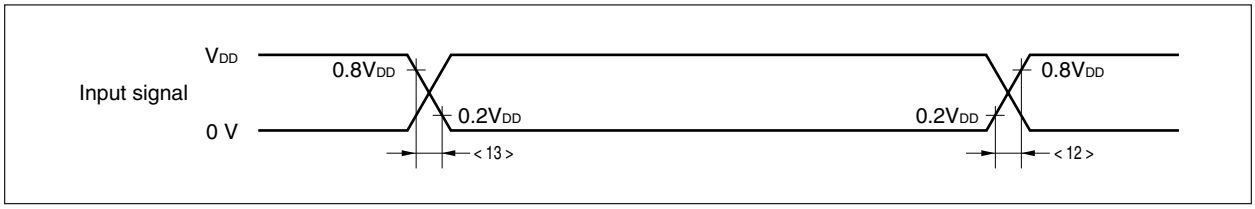
Remark T = t_{CYK}



(2) Input wave

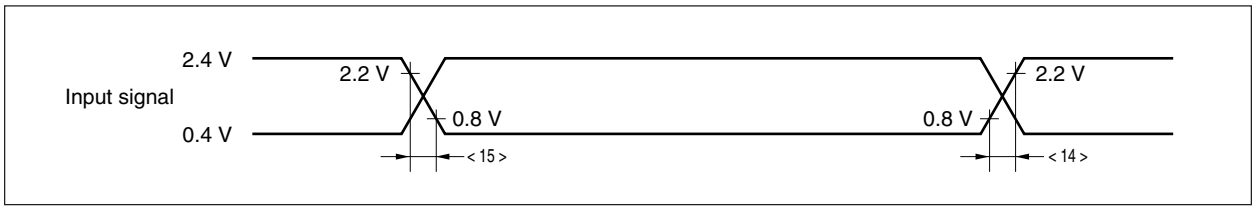
(a) P02 to P07, P12 to P17, P23, P24, P26, P27, P32 to P37, P112 to P117, $\overline{\text{RESET}}$, NMI, MODE, and their alternate-function pins

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Input rise time	<12>	t_{IR2}			20	ns
Input fall time	<13>	t_{IF2}			20	ns



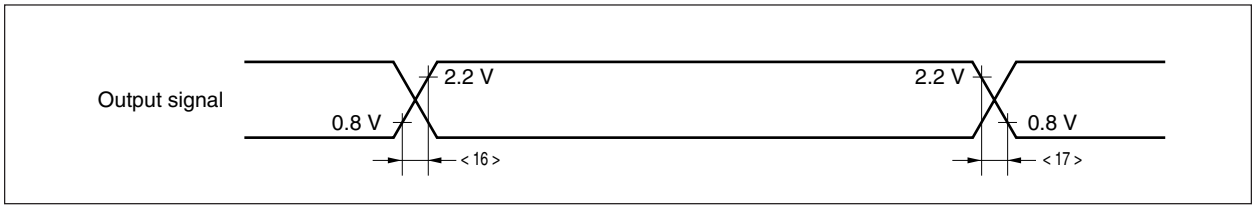
(b) Other than (a)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Input rise time	<14>	t_{IR1}			10	ns
Input fall time	<15>	t_{IF1}			10	ns



(3) Output wave (other than CLKOUT)

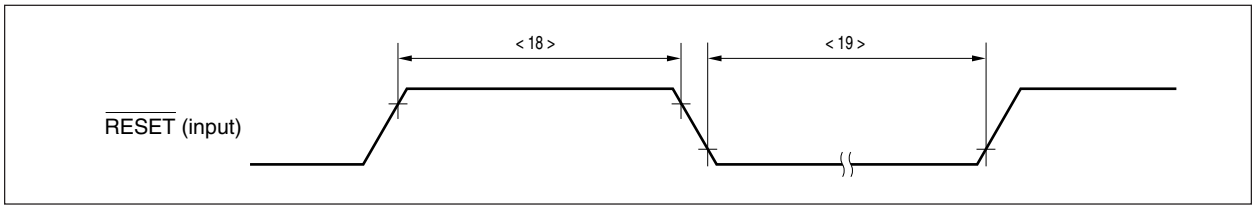
Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Output rise time	<16>	t_{OR}			10	ns
Output fall time	<17>	t_{OF}			10	ns



(4) Reset timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{\text{RESET}}$ width, high	<18>	t_{WRSH}		500		ns
$\overline{\text{RESET}}$ width, low	<19>	t_{WRSL}	On power application, or on releasing STOP mode	500 + T_{OST}		ns
			Except on power application, or except on releasing STOP mode	500		ns

Remark T_{OST}: Oscillation stabilization time



(5) Read timing (1/2)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<20>	t_{DKA}		3	20	ns
Delay time from CLKOUT↑ to R/$\overline{W}$, $\overline{UBEN}$, $\overline{LBEN}$	<78>	t_{DKA2}		–2	+13	ns
Delay time from CLKOUT↑ to address float	<21>	t_{FKA}		3	15	ns
Delay time from CLKOUT↓ to ASTB	<22>	t_{DKST}		3	15	ns
Delay time from CLKOUT↓ to $\overline{DSTB}$	<23>	t_{DKD}		3	15	ns
Data input setup time (to CLKOUT↑)	<24>	t_{SIDK}		5		ns
Data input hold time (from CLKOUT↑)	<25>	t_{HKID}		5		ns
$\overline{WAIT}$ setup time (to CLKOUT↓)	<26>	t_{SWTK}		5		ns
$\overline{WAIT}$ hold time (from CLKOUT↓)	<27>	t_{HKWT}		5		ns
Address hold time (from CLKOUT↑)	<28>	t_{HKA}		0		ns
Address setup time (to ASTB↓)	<29>	t_{SAST}	$-40°C \le T_A \le +70°C$	0.5 T – 10		ns
			$70°C < T_A \le 85°C$	0.5 T – 12		ns
Address hold time (from ASTB↓)	<30>	t_{HSTA}		0.5 T – 10		ns
Delay time from $\overline{DSTB}$↓ to address float	<31>	t_{FDA}			0	ns
Data input setup time (to address)	<32>	t_{SAID}	$-40°C \le T_A \le +70°C$		(2 + n) T – 22	ns
			$70°C < T_A \le 85°C$		(2 + n) T – 25	ns
Data input setup time (to $\overline{DSTB}$↓)	<33>	t_{SDID}	$-40°C \le T_A \le +70°C$		(1 + n) T – 20	ns
			$70°C < T_A \le 85°C$		(1 + n) T – 24	ns
Delay time from ASTB↓ to $\overline{DSTB}$↓	<34>	t_{DSTD}		0.5 T – 10		ns
Data input hold time (from $\overline{DSTB}$↑)	<35>	t_{HDID}		0		ns
Delay time from $\overline{DSTB}$↑ to address output	<36>	t_{DDA}		(1 + i) T		ns
Delay time from $\overline{DSTB}$↑ to ASTB↑	<37>	t_{DDSTH}		0.5 T – 10		ns
Delay time from $\overline{DSTB}$↑ to ASTB↓	<38>	t_{DDSTL}		(1.5 + i) T – 10		ns
$\overline{DSTB}$ low-level width	<39>	t_{WDL}	$-40°C \le T_A \le +70°C$	(1 + n) T – 10		ns
			$70°C < T_A \le 85°C$	(1 + n) T – 13		ns
ASTB high-level width	<40>	t_{WSTH}		T – 10		ns
$\overline{WAIT}$ setup time (to address)	<41>	t_{SAWT1}	$n \ge 1, -40°C \le T_A \le +70°C$		1.5 T – 20	ns
			$n \ge 1, 70°C < T_A \le 85°C$		1.5 T – 24	ns
	<42>	t_{SAWT2}	$n \ge 1, -40°C \le T_A \le +70°C$		(1.5 + n) T – 20	ns
			$n \ge 1, 70°C < T_A \le 85°C$		(1.5 + n) T – 24	ns
$\overline{WAIT}$ hold time (from address)	<43>	t_{HAWT1}	$n \ge 1$	(0.5 + n) T		ns
	<44>	t_{HAWT2}	$n \ge 1$	(1.5 + n) T		ns
$\overline{WAIT}$ setup time (to ASTB↓)	<45>	t_{SSTWT1}	$n \ge 1, -40°C \le T_A \le +70°C$		T – 18	ns
			$n \ge 1, 70°C < T_A \le 85°C$		T – 20	ns
	<46>	t_{SSTWT2}	$n \ge 1$		(1 + n) T – 15	ns
$\overline{WAIT}$ hold time (from ASTB↓)	<47>	t_{HSTWT1}	$n \ge 1$	nT		ns
	<48>	t_{HSTWT2}	$n \ge 1$	(1 + n) T		ns

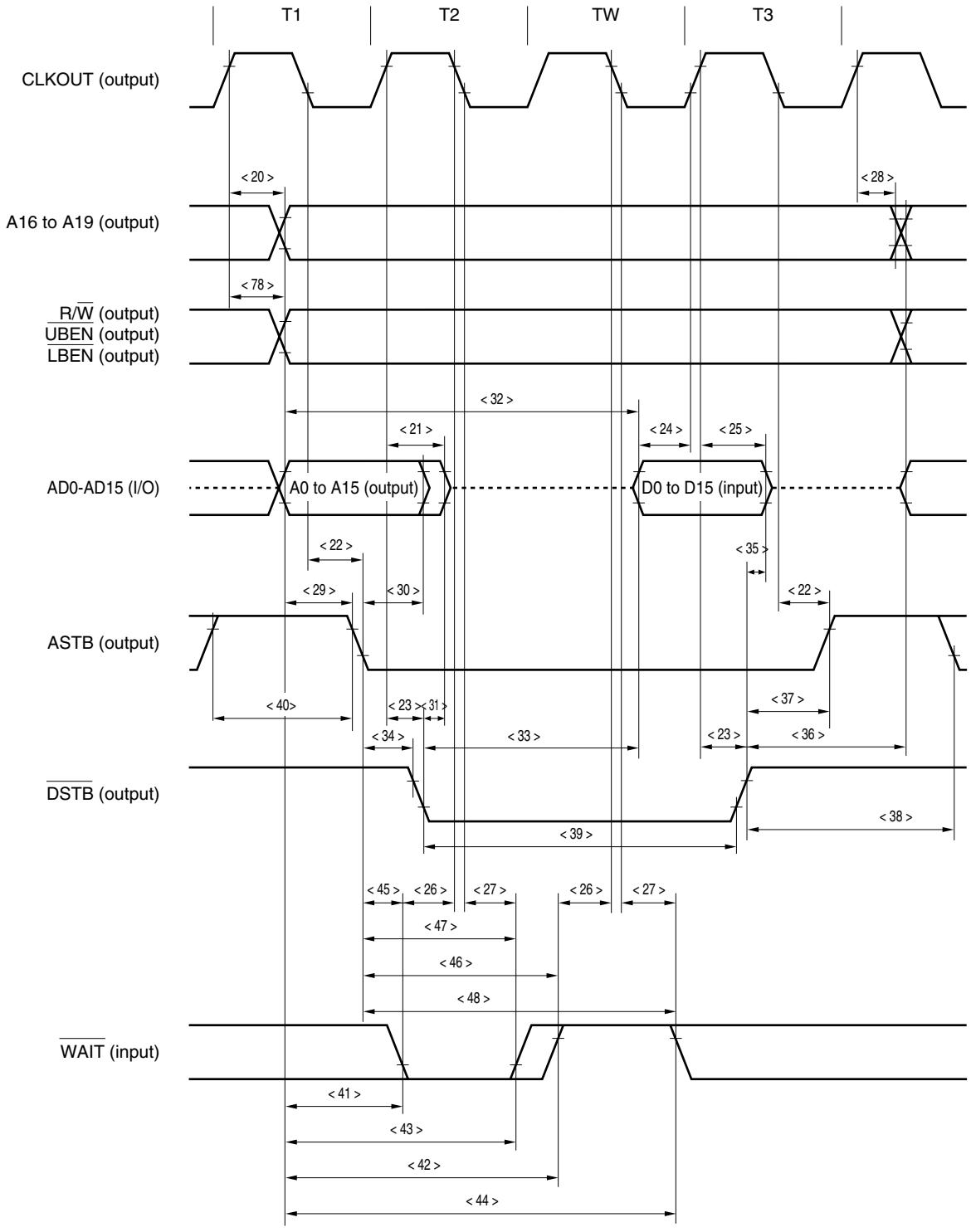
Remarks 1. T = t_{CYK}

2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.

3. i indicates the number of idle states (0 or 1) t be inserted in the read cycle.

4. Be sure to observe at least one of data input hold times t_{HKID} (<25>) and t_{HDID} (<35>).

(5) Read Timing (2/2): 1 wait



Remark Broken line indicates high-impedance.

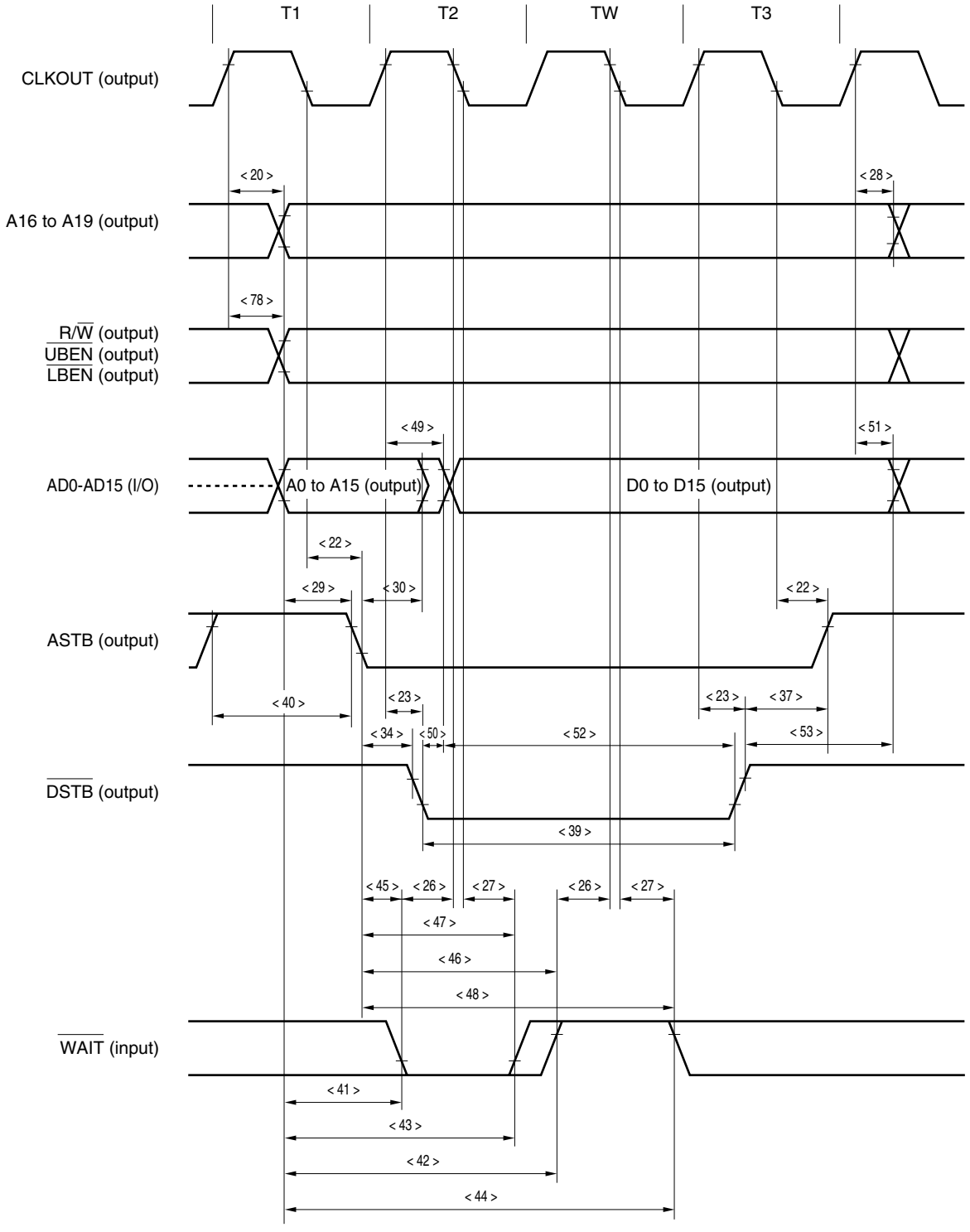
(6) Write timing (1/2)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<20>	t_{DKA}		3	20	ns
Delay time from CLKOUT↑ to R/$\overline{W}$, $\overline{UBEN}$, $\overline{LBEN}$	<78>	t_{DKA2}		–2	+13	ns
Delay time from CLKOUT↓ to ASTB	<22>	t_{DKST}		3	15	ns
Delay time from CLKOUT↑ to $\overline{DSTB}$	<23>	t_{DKD}		3	15	ns
$\overline{WAIT}$ setup time (to CLKOUT↓)	<26>	t_{SWTK}		5		ns
$\overline{WAIT}$ hold time (from CLKOUT↓)	<27>	t_{HKWT}		5		ns
Address hold time (from CLKOUT↑)	<28>	t_{HKA}		0		ns
Address setup time (to ASTB↓)	<29>	t_{SAST}	$-40°C \le T_A \le +70°C$	0.5 T – 10		ns
			$70°C < T_A \le 85°C$	0.5 T – 12		ns
Address hold time (from ASTB↓)	<30>	t_{HSTA}		0.5 T – 10		ns
Delay time from ASTB↓ to $\overline{DSTB}$↓	<34>	t_{DSTD}		0.5 T – 10		ns
Delay time from DSTB↑ to $\overline{ASTB}$↑	<37>	t_{DDSTH}		0.5 T – 10		ns
$\overline{DSTB}$ low-level width	<39>	t_{WDL}	$-40°C \le T_A \le +70°C$	(1 + n) T – 10		ns
			$70°C < T_A \le 85°C$	(1 + n) T – 13		ns
$\overline{ASTB}$ high-level width	<40>	t_{WSTH}		T – 10		ns
$\overline{WAIT}$ setup time (to address)	<41>	t_{SAWT1}	$n \ge 1, -40°C \le T_A \le +70°C$		1.5 T – 20	ns
			$n \ge 1, 70°C < T_A \le 85°C$		1.5 T – 24	ns
	<42>	t_{SAWT2}	$n \ge 1, -40°C \le T_A \le +70°C$		(1.5 + n) T – 20	ns
			$n \ge 1, 70°C < T_A \le 85°C$		(1.5 + n) T – 24	ns
$\overline{WAIT}$ hold time (from address)	<43>	t_{HAWT1}	$n \ge 1$	(0.5 + n) T		ns
	<44>	t_{HAWT2}	$n \ge 1$	(1.5 + n) T		ns
$\overline{WAIT}$ setup time (to ASTB↓)	<45>	t_{SSTWT1}	$n \ge 1, -40°C \le T_A \le +70°C$		T – 18	ns
			$n \ge 1, 70°C < T_A \le 85°C$		T – 20	ns
	<46>	t_{SSTWT2}	$n \ge 1$		(1 + n) T – 15	ns
$\overline{WAIT}$ hold time (from ASTB↓)	<47>	t_{HSTWT1}	$n \ge 1$	nT		ns
	<48>	t_{HSTWT2}	$n \ge 1$	(1 + n) T		ns
Address hold time (from CLKOUT↑)	<49>	t_{DKOD}	$-40°C \le T_A \le +70°C$		20	ns
			$70°C < T_A \le 85°C$		23	ns
Delay time from $\overline{DSTB}$↓ to data output	<50>	t_{DDOD}			10	ns
Data output hold time (from CLKOUT↑)	<51>	t_{HKOD}		0		ns
Data output setup time (to $\overline{DSTB}$↑)	<52>	t_{SODD}		(1 + n) T – 15		ns
Data output hold time (from $\overline{DSTB}$↑)	<53>	t_{HDOD}		T – 10		ns

Remarks 1. $T = t_{CYK}$

2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.

(6) Write timing (2/2): 1 wait



Remark Broken line indicates high-impedance.

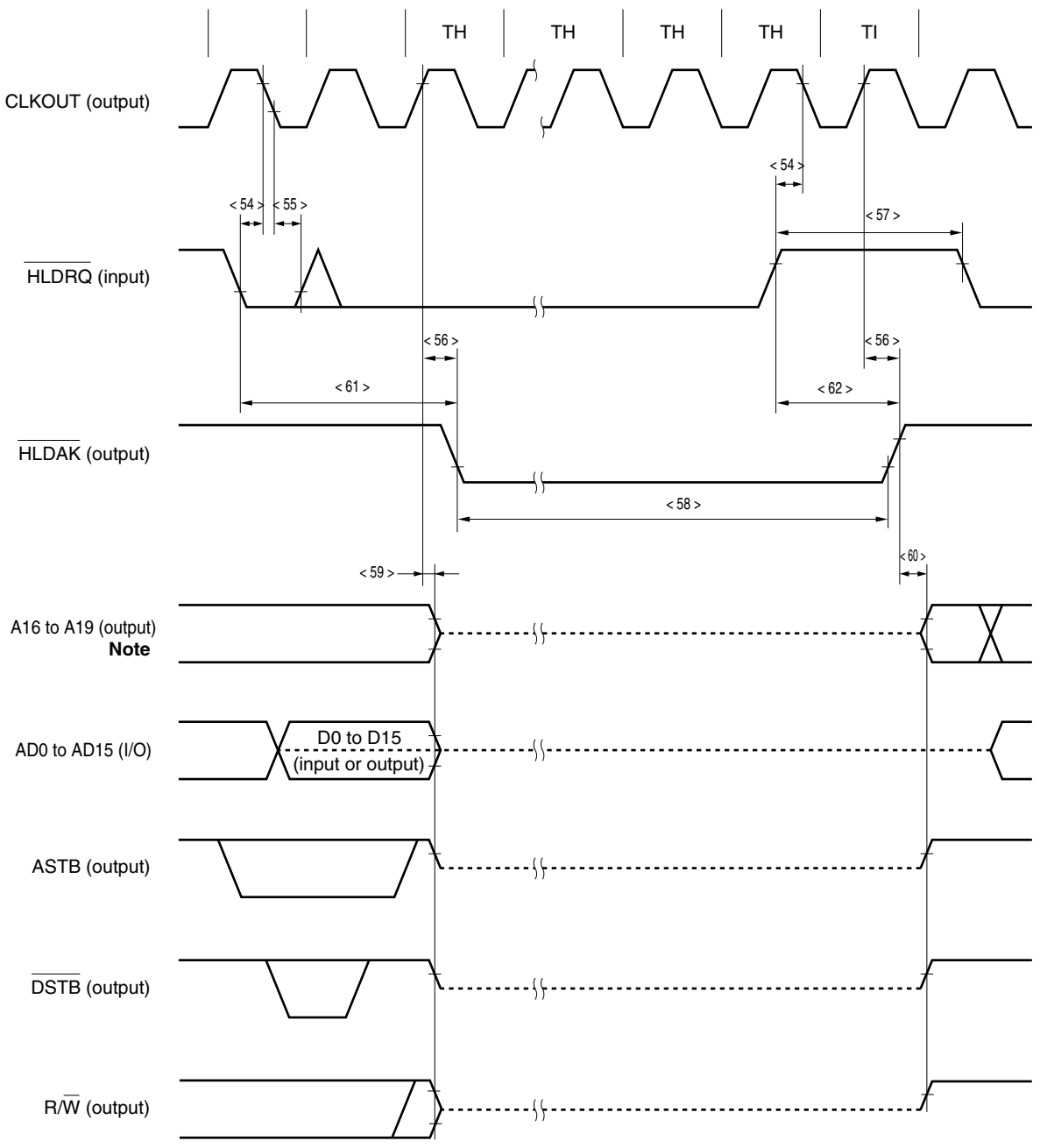
(7) Bus hold timing (1/2)

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{\text{HLDRQ}}$ setup time (to CLKOUT↓)	<54>	t_{SHOK}		5		ns
$\overline{\text{HLDRQ}}$ hold time (from CLKOUT↓)	<55>	t_{HKHQ}		5		ns
Delay time from $\overline{\text{HLDAK}}$ to CLKOUT↑	<56>	t_{DKHA}			20	ns
$\overline{\text{HLDRQ}}$ high-level width	<57>	t_{WHQH}		T + 10		ns
$\overline{\text{HLDAK}}$ low-level width	<58>	t_{WHAL}	$-40°C \le T_A \le +70°C$	T – 10		ns
			$70°C < T_A \le 85°C$	T – 12		ns
Delay time from CLKOUT↑ to bus float	<59>	t_{DKF}			20	ns
Delay time from $\overline{\text{HLDAK}}$↑ to bus output	<60>	t_{DHAC}		–3		ns
Delay time from $\overline{\text{HLDRQ}}$↓ to $\overline{\text{HLDAK}}$↓	<61>	t_{DHQHA1}			(2 n + 7.5) T + 20	ns
Delay time from $\overline{\text{HLDRQ}}$↑ to $\overline{\text{HLDAK}}$↑	<62>	t_{DHQHA2}		0.5 T	1.5 T + 20	ns

Remarks 1. $T = t_{CYK}$

2. n indicates the number of wait clocks inserted in the bus cycle. The sampling timing differs when the programmable wait state is inserted.

(7) Bus hold timing (2/2)



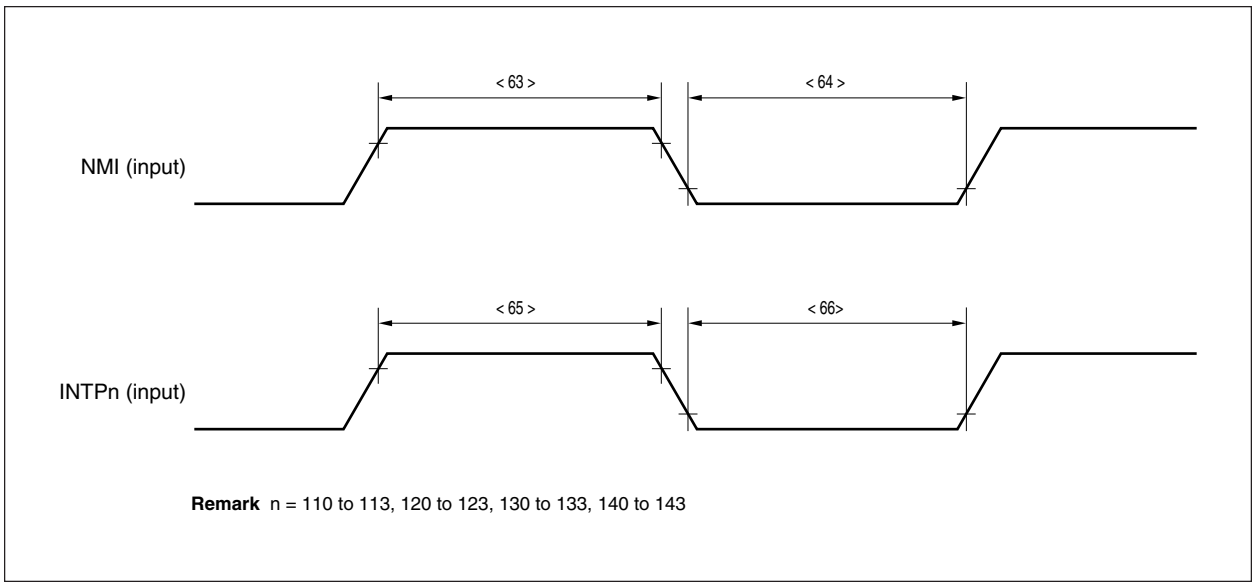
Note UBEN (output), LBEN (output)

Remark Broken line indicates high-impedance.

(8) Interrupt timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
NMI width, high	<63>	t_{WNIH}		500		ns
NMI width, low	<64>	t_{WNIL}		500		ns
INTPn width, high	<65>	t_{WITH}	n = 110 to 113, 120 to 123, 130 to 133, 140 to 143	3 T + 10		ns
INTPn width, low	<66>	t_{WITL}	n = 110 to 113, 120 to 123, 130 to 133, 140 to 143	3 T + 10		ns

Remark T = t_{CYK}



Remark n = 110 to 113, 120 to 123, 130 to 133, 140 to 143

(9) CSI timing (1/2)

(a) Master mode

(i) CSI0 to CSI2 timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCKn}$ cycle	<67>	t_{CYSK1}	Output	120		ns
$\overline{SCKn}$ high-level width	<68>	t_{WSKH1}	Output	0.5 t_{CYSK1} – 20		ns
$\overline{SCKn}$ low-level width	<69>	t_{WSKL1}	Output	0.5 t_{CYSK1} – 20		ns
SIn setup time (to $\overline{SCKn}$↑)	<70>	t_{SSISK1}		30		ns
SIn hold time (from $\overline{SCKn}$↑)	<71>	t_{HSKSI1}		0		ns
SOn output delay time (from $\overline{SCKn}$↓)	<72>	t_{DSKSO1}			18	ns
SOn output hold time (from $\overline{SCKn}$↑)	<73>	t_{HSKSO1}		0.5 t_{CYSK1} – 5		ns

Remark n = 0 to 2

(ii) CSI3 timing

Parameter	Symbol		Conditions		MIN.	MAX.	Unit
$\overline{SCK3}$ cycle	<67>	t_{CYSK3}	Output	R_L = 1.5 kΩ C_L = 50 pF	500		ns
$\overline{SCK3}$ high-level width	<68>	t_{WSKH3}	Output		0.5 t_{CYSK3} – 70		ns
$\overline{SCK3}$ low-level width	<69>	t_{WSKL3}	Output		0.5 t_{CYSK3} – 70		ns
SI3 setup time (to $\overline{SCK3}$↑)	<70>	t_{SSISK3}			100		ns
SI3 hold time (from $\overline{SCK3}$↑)	<71>	t_{HSKSI3}			50		ns
SO3 output delay time (from $\overline{SCK3}$↓)	<72>	t_{DSKSO3}	R_L = 1.5 KΩ C_L = 50 pF			150	ns
SO3 output hold time (from $\overline{SCK3}$↑)	<73>	t_{HSKSO3}			0.5 t_{CYSK3} – 5		ns

Remark R_L and C_L are the load resistance and load capacitance respectively of the $\overline{SCK3}$ and SO3 output lines.

(b) Slave mode

(i) CSI0 to CSI2 timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCKn}$ cycle	<67>	t_{CYSK2}	Input	120		ns
$\overline{SCKn}$ high-level width	<68>	t_{WSKH2}	Input	30		ns
$\overline{SCKn}$ low-level width	<69>	t_{WSKL2}	Input	30		ns
SIn setup time (to $\overline{SCKn}$↑)	<70>	t_{SSISK2}		10		ns
SIn hold time (from $\overline{SCKn}$↑)	<71>	t_{HSKSI2}		10		ns
SOn output delay time (from $\overline{SCKn}$↓)	<72>	t_{DSKSO2}			30	ns
SOn output hold time (from $\overline{SCKn}$↑)	<73>	t_{HSKSO2}		t_{WSKH2}		ns

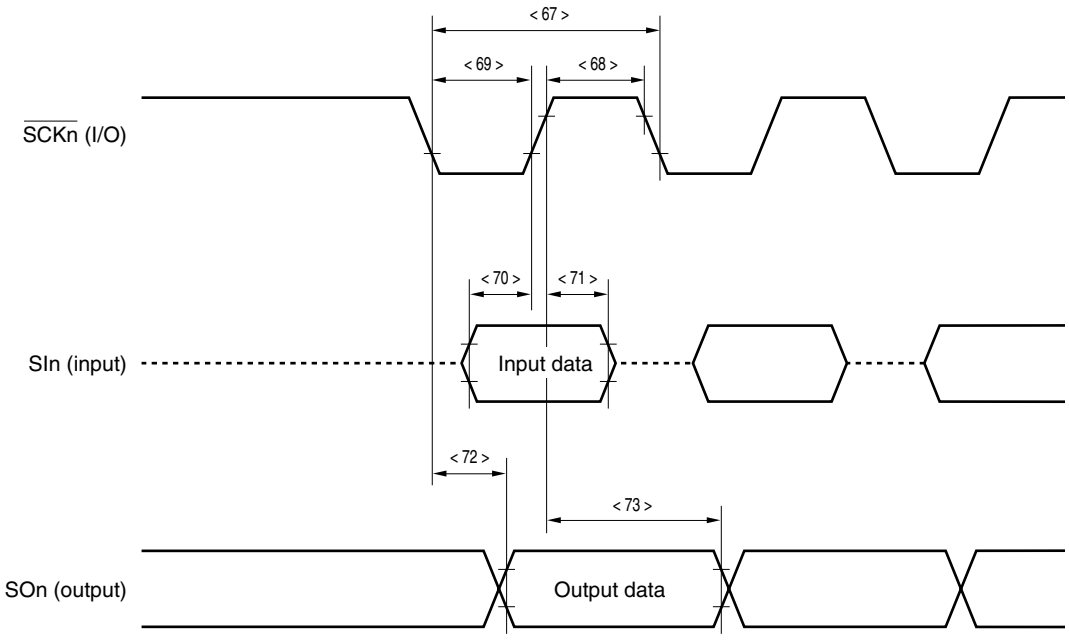
Remark n = 0 to 2

(9) CSI timing (2/2)

(ii) CSI3 timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
$\overline{SCK3}$ cycle	<67>	t_{CYSK4}	Input	500		ns
$\overline{SCK3}$ high-level width	<68>	t_{WSKH4}	Input	180		ns
$\overline{SCK3}$ low-level width	<69>	t_{WSKL4}	Input	180		ns
SI3 setup time (to $\overline{SCK3}\uparrow$)	<70>	t_{SSISK4}		100		ns
SI3 hold time (from $\overline{SCK3}\uparrow$)	<71>	t_{HSKSI4}		50		ns
SO3 output delay time (from $\overline{SCK3}\downarrow$)	<72>	t_{DSKSO4}	R_L = 1.5 kΩ		150	ns
SO3 output hold time (from $\overline{SCK3}\uparrow$)	<73>	t_{HSKSO4}	C_L = 50 pF	t_{WSKH4}		ns

Remark R_L and C_L are the load resistance and load capacitance respectively of the $\overline{SCK3}$ and SO3 output lines.

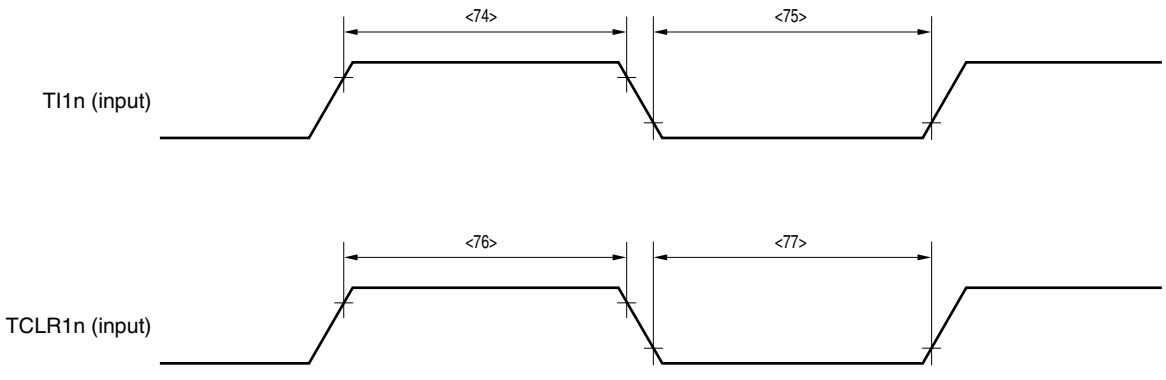


Remark 1. The broken line indicates the high-impedance state.
2. n = 0 to 3

(10) RPU timing

Parameter	Symbol		Conditions	MIN.	MAX.	Unit
TI1n high-level width	<74>	t_{WTIH}		3 T + 10		ns
TI1n low-level width	<75>	t_{WTIL}		3 T + 10		ns
TCLR1n high-level width	<76>	t_{WTCH}		3 T + 10		ns
TCLR1n low-level width	<77>	t_{WTCL}		3 T + 10		ns

Remark T = t_{CYK}



Remark n = 1 to 4

A/D Converter Characteristics (T_A = –40 to +85°C, V_{DD} = AV_{DD} = 5 V ±10%, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	—		10	10	10	bit
Overall error[Note 1]	—	4.5 V ≤ AV_{REF1} ≤ AV_{DD}			±0.4	%FSR
	—	3.5 V ≤ AV_{REF1} ≤ AV_{DD}			±0.7	%FSR
Quantization error	—				±1/2	LSB
Conversion time	t_{CONV}	4.5 V ≤ AV_{REF1} ≤ AV_{DD}	60			t_{CYK}
		3.5 V ≤ AV_{REF1} ≤ AV_{DD}	60			t_{CYK}
Sampling time	t_{SAMP}	4.5 V ≤ AV_{REF1} ≤ AV_{DD}	10			t_{CYK}
		3.5 V ≤ AV_{REF1} ≤ AV_{DD}	10			t_{CYK}
Zero-scale error[Note 1]	—	4.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±3.5	LSB
	—	3.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±4.5	LSB
Full-scale error[Note 1]	—	4.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±2.5	LSB
	—	3.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±4.5	LSB
Non-linearity error[Note 1]	—	4.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±2.5	LSB
	—	3.5 V ≤ AV_{REF1} ≤ AV_{DD}		±1.5	±4.5	LSB
Analog input voltage[Note 2]	V_{IAN}		–0.3		AV_{DD} + 0.3	V
Reference voltage	AV_{REF1}		3.5		AV_{DD}	V
AV_{REF1} current	AI_{REF1}			1.2	3.0	mA
AV_{DD} supply current	AI_{DD}			2.3	6.0	mA

Notes 1. Except quantization error.

2. The conversion result is 000H when V_{IAN} = 0.
Converted with 10-bit resolution when 0 < V_{IAN} < AV_{REF1}.
The conversion result is 3FFH when AV_{REF1} ≤ V_{IAN} ≤ AV_{DD}.

D/A Converter Characteristics (T_A = –40 to +85°C, V_{DD} = AV_{DD} = 5 V ±10%, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	—		8	8	8	bit
Overall error	—	Load conditions: 2 MΩ, 30 pF AV_{REF2} = V_{DD} AV_{REF3} = 0			0.8	%
	—	Load conditions: 2 MΩ, 30 pF AV_{REF2} = 0.75 V_{DD} AV_{REF3} = 0.25 V_{DD}			1.0	%
	—	Load conditions: 4 MΩ, 30 pF AV_{REF2} = V_{DD} AV_{REF3} = 0			0.6	%
	—	Load conditions: 4 MΩ, 30 pF AV_{REF2} = 0.75 V_{DD} AV_{REF3} = 0.25 V_{DD}			0.8	%
Settling time	—	Load conditions: 2 MΩ, 30 pF			10	μs
Output resistance	RO			8		kΩ
AV_{REF2} input voltage	AV_{REF2}		0.75V_{DD}		V_{DD}	V
AV_{REF3} input voltage	AV_{REF3}		0		0.25V_{DD}	V
Resistance between AV_{REF2} and AV_{REF3}	R_{AIREF}	DACS0, DACS1 = 55H	2	4		kΩ

3.2 Flash Memory Programming Mode

Basic Characteristics (T_A = 10 to 40°C (when rewriting), T_A = –40 to +85°C (when not rewriting), V_{DD} = AV_{DD} = 5 V ±10%, V_{SS} = AV_{SS} = 0 V))

(1) μPD70F3003A (all ranks), 70F3025A (except K, E, P, X rank)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating frequency	ϕ		10		33	MHz
V_{PP} supply voltage	V_{PP1}	During flash memory programming	9.7	10.3	10.6	V
	V_{PPL}	V_{PP} low-level detection	–0.5		$0.2V_{DD}$	V
	V_{PPM}	V_{PP}, V_{DD} level detection	$0.8V_{DD}$		$1.2V_{DD}$	V
	V_{PPH}	V_{PP} high-voltage level detection	9.7	10.3	10.6	V
V_{DD} supply current	I_{DD}	V_{PP} = V_{PP1}			$3.0 \times \phi + 25$	mA
V_{PP} supply current	I_{PP}	V_{PP} = 10.3 V			200	mA
Step erase time	t_{ER}	**Note 1**		0.2		s
Overall erase time per area	t_{ERA}	When the step erase time = 0.2 s, **Note 2**			40	s/area
Write-back time	t_{WB}	**Note 3**		5		ms
Number of write-backs per write-back command	C_{WB}	When the write-back time = 5 ms, **Note 4**			50	Count/write-back command
Number of erase/write-backs	C_{ERWB}				16	Count
Step writing time	t_{WT}	**Note 5**		50		μs
Overall writing time per word	t_{WTW}	When the step writing time = 50 μs (1 word = 4 bytes), **Note 6**	50		500	μs/word
Number of rewrites per area	C_{ERWR}	1 erase + 1 write after erase = 1 rewrite, **Note 7**		20		Count/area

Notes 1. The recommended setting value of the step erase time is 0.2 s.

2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.

3. The recommended setting value of the step erase time is 5 ms.

4. Write-back is executed once by the issuance of the write-back command. Therefore, the retry count must be the maximum value minus the number of commands issued.

5. The recommended setting value of the step writing time is 50 μs.

6. 100 μs is added to the actual writing time per word. The internal verify time during and after the writing is not included.

7. When writing initially to shipped products, it is counted as one rewrite for both “erase to write” and “write only”.

Example (P: Write, E: Erase)

Shipped product ⟶ P→ E → P → E → P: 3 rewrites

Shipped product → E → P → E → P → E → P: 3 rewrites

Cautions 1. V_{PP} pull-down resistance value (RV_{PP}) is recommended to be in the range 5 kΩ to 15 kΩ.

2. Set the transfer rate between programmer and device as follows.

CSI0: 0.2 to 1 MHz

UART0: 4,800 to 76,800 bps

Remarks 1. When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.

2. Area 0 = 00000H to 1FFFFH, area 1 = 20000H to 3FFFFH (area 1 is provided in the μPD70F3025A only)

3. The rank is indicated by the 5th character from the left in the lot number.

4. The I rank applies to engineering samples (ES) only. The operation of an ES is not guaranteed.

5. ϕ: Internal system clock frequency

(2) μPD70F3025A (X rank)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Operating frequency	ϕ	**Note 1**	10		33	MHz
V_{PP} supply voltage	V_{PP1}	During flash memory programming	9.7	10.3	10.6	V
	V_{PPL}	V_{PP} low-level detection	–0.5		$0.2V_{DD}$	V
	V_{PPM}	V_{PP}, V_{DD} level detection	$0.8V_{DD}$		$1.2V_{DD}$	V
	V_{PPH}	V_{PP} high-voltage level detection	9.7	10.3	10.6	V
V_{DD} supply current	I_{DD}	$V_{PP}= V_{PP1}$			$3.0 \times \phi + 25$	mA
V_{PP} supply current	I_{PP}	V_{PP}= 10.3 V			200	mA
Step erase time	t_{ER}	**Note 1**		2		s
Overall erase time per area	t_{ERA}	When the step erase time = 2 s, **Note 2**			40	s/area
Step writing time	t_{WT}	**Note 3**		200		μs
Overall writing time per word	t_{WTW}	When the step writing time = 200 μs (1 word = 4 bytes), **Note 4**	200		2000	μs/word
Number of rewrites per area	C_{ERWR}	1 erase + 1 write after erase = 1 rewrite, **Note 5**	20			Count/area

Notes 1. The recommended setting value of the step erase time is 2 s.

2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.

3. The recommended setting value of the step writing time is 200 μs.

4. 100 μs is added to the actual writing time per word. The internal verify time during and after the writing is not included.

5. When writing initially to shipped products, it is counted as one rewrite for both “erase to write” and “write only”.

Example (P: Write, E: Erase)

Shipped product ⟶ P → E → P → E → P: 3 rewrites

Shipped product → E → P → E → P → E → P: 3 rewrites

Cautions 1. V_{PP} pull-down resistance value (RV_{PP}) is recommended to be in the range 5 kΩ to 15 kΩ.

2. Set the transfer rate between programmer and device as follows.

CSI0: 0.2 to 1 MHz

UART0: 4,800 to 76,800 bps

Remarks 1. When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.

2. Area 0 = 00000H to 1FFFFH, area 1 = 20000H to 3FFFFH

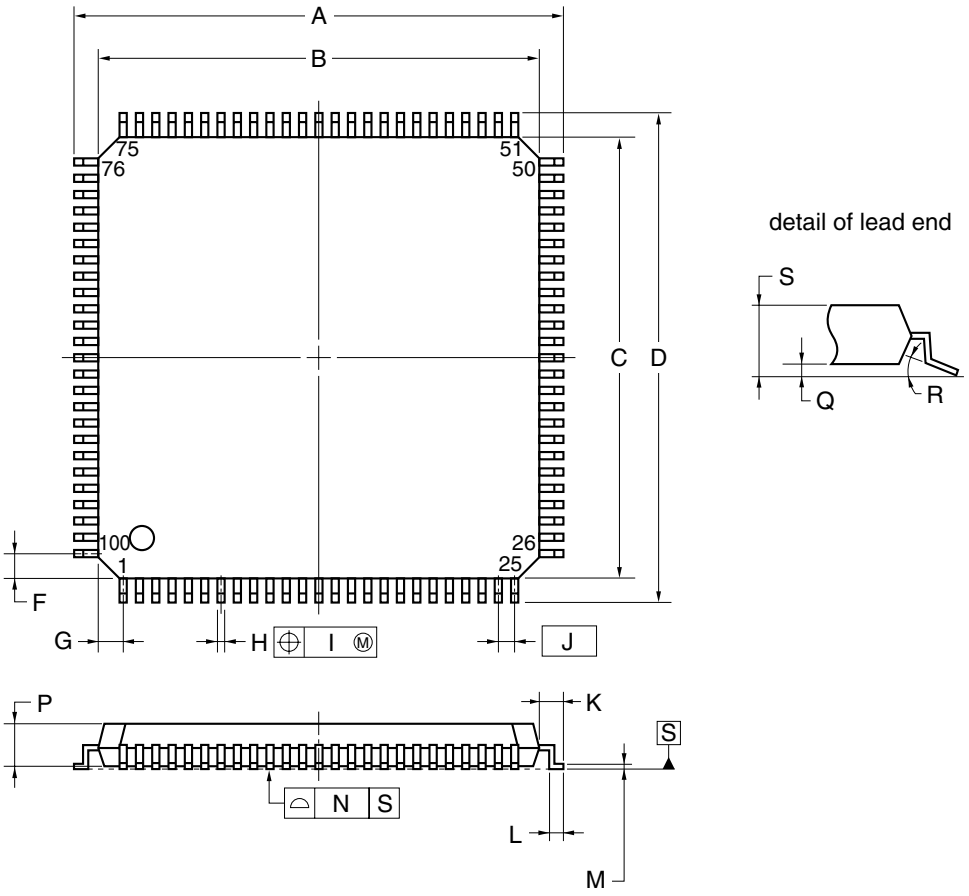
3. The rank is indicated by the 5th character from the left in the lot number.

4. The K, E, P, and X rank products do not support handshake mode. The I rank applies to engineering samples (ES) only. The operation of an ES is not guaranteed.

5. ϕ: Internal system clock frequency

★ 4. PACKAGE DRAWING

100-PIN PLASTIC LQFP (FINE PITCH) (14x14)



NOTE

Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	16.00±0.20
B	14.00±0.20
C	14.00±0.20
D	16.00±0.20
F	1.00
G	1.00
H	$0.22^{+0.05}_{-0.04}$
I	0.08
J	0.50 (T.P.)
K	1.00±0.20
L	0.50±0.20
M	$0.17^{+0.03}_{-0.07}$
N	0.08
P	1.40±0.05
Q	0.10±0.05
R	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$
S	1.60 MAX.

S100GC-50-8EU, 8EA-2

5. RECOMMENDED SOLDERING CONDITIONS

The μPD70F3003A, 70F3025A, and 70F3003A(A) should be soldered and mounted under the following recommended conditions.

For details of the recommended soldering conditions, refer to the document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact an NEC sales representative.

Table 5-1. Soldering Mounting Type Soldering Conditions

(1) μPD70F3003AGC-33-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)
μPD70F3025AGC-33-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Three times or less, Exposure limit: 3 days[Note] (after that, prebake at 125°C for 10 to 72 hours)	IR35-103-3
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Three times or less, Exposure limit: 3 days[Note] (after that, prebake at 125°C for 10 to 72 hours)	VP15-103-3
Partial heating	Pin temperature: 300°C max., Time 3 seconds max. (per pin row)	—

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

★ **(2) μPD70F3003AGC(A)-33-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)**

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less, Exposure limit: 3 days[Note] (after that, prebake at 125°C for 10 to 72 hours)	IR35-103-2
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Two times or less, Exposure limit: 3 days[Note] (after that, prebake at 125°C for 10 to 72 hours)	VP15-103-2
Partial heating	Pin temperature: 300°C max., Time 3 seconds max. (per pin row)	—

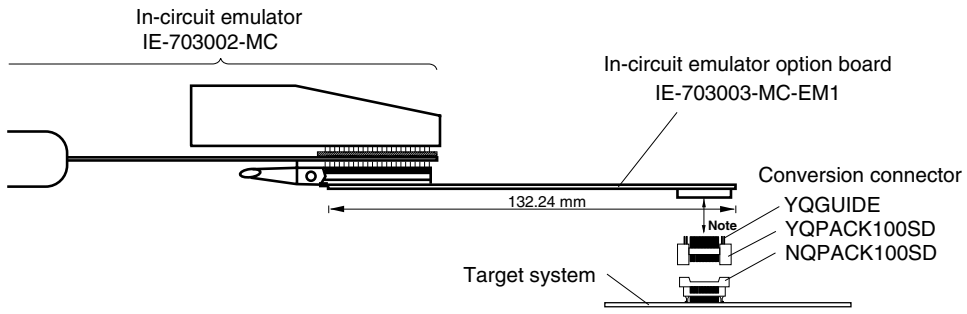
Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

★ APPENDIX NOTES ON TARGET SYSTEM DESIGN

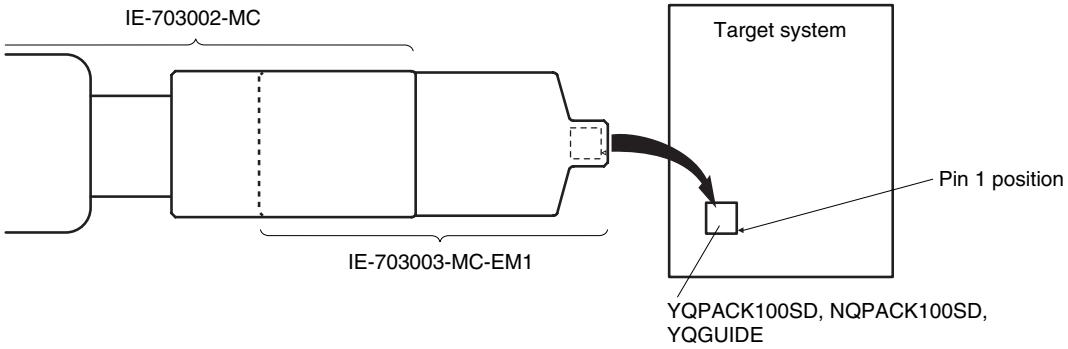
The following shows a diagram of the connection conditions between the in-circuit emulator option board and conversion connector. Design your system making allowances for conditions such as the form of parts mounted on the target system as shown below.

Side view

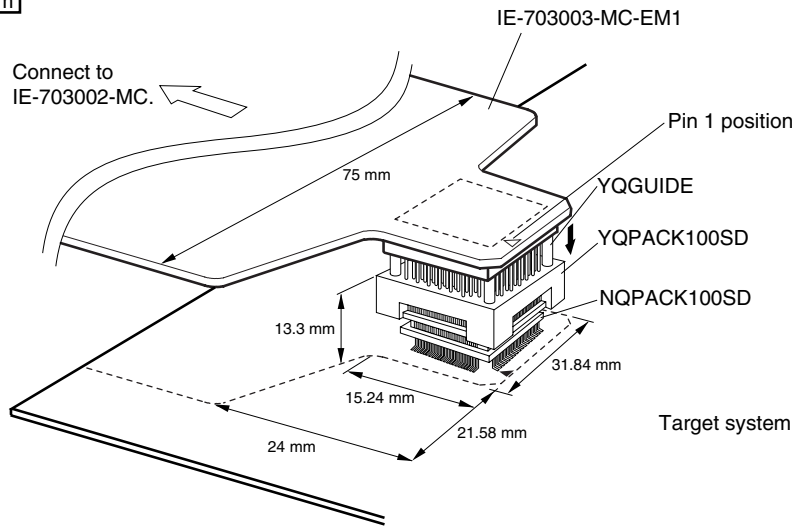


Note YQSOCKET100SDN (included with IE-703002-MC) can be inserted here to adjust the height (height: 3.2 mm).

Top view



Connection condition diagram



[MEMO]

[MEMO]

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

Related document: μPD703003A, 703004A, 703025A, 703003A(A), 703025A(A) Data Sheet (U13188E)

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